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U.S. Patent Documents

Examiner Initial	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE

Foreign Patent Documents

Examiner Initial	DOCUMENT NUMBER	FILING DATE	COUNTRY	CLASS	SUB-CLASS	TRANSLATION	
						Yes	No
GA	2003-78213	9/5/2001	Japan			Abstract	X
GA	2001-102355	7/26/2000	Japan			Abstract	X
GA	10-335756	6/5/97	Japan			Abstract	X

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

SA	M. Aoki et al., "85°C-10Gbit/s Operation of 1.30µm InGaAlAs MQW-DFB Laser", 26 th European conference (ECOC2000), Vol 1, 2 pages
I	P.J.A. Thijs et al., "High Performance Buried Heterostructure λ = 1.5 µm InGaAs/AlGaInAs Strained-Layer Quantum Well Laser Diodes", International Conference on Indium Phosphide and Related Materials, Conference Proceedings 1996, pp. 765-768
I	K. Shinoda et al., "Highly Reliable InGaAsP/InP Lasers with Defect-Free Regrowth Interfaces formed by Newly Composed HBr-Based Solutions", 2001 IEEE, 2001 International Conference on Indium Phosphide and Related Materials, pp. 409-412
SA	D. Bertone et al., "High Reliability, High Yield, High Modulation Bandwidth, Low Threshold Current 1.55 µm MQW Laser by New In-Situ Etching Technique", 24 th European Conference on Optical Communication (ECOC 1998) Proceedings, Vol. 1, pp. 75-76

EXAMINER

Samuel

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EXAMINER: Initial if citation is considered, whether or not citation is in conformance with MPEP 609; draw a line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant